Average gate power dissipation (T_j=125)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	4	kV

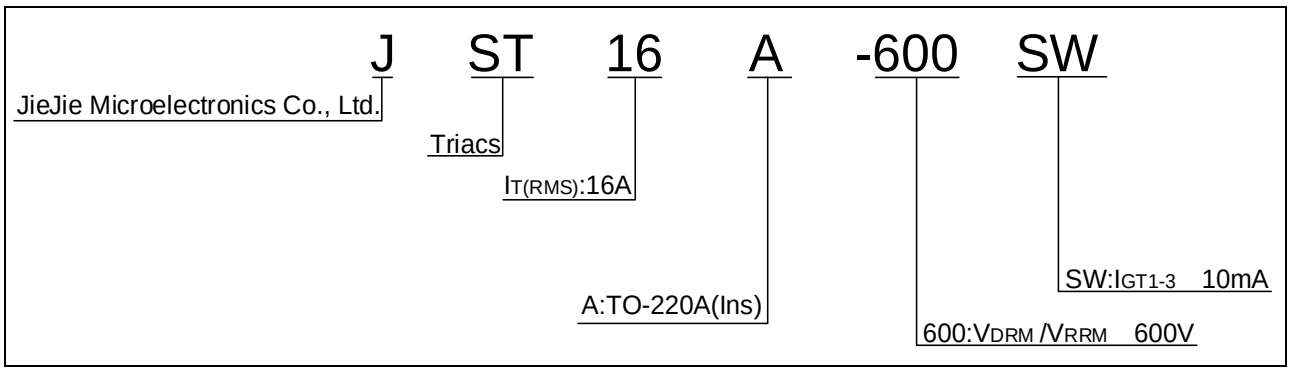
ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	10	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3kΩ	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	25	mA
				30	
I_H	I_T =500mA		MAX.	15	mA
dV/dt	V_D=400V Gate Open T_j =125		MIN.	500	V/μs
(dI/dt)c	(dV/dt)c=10V/μs T_j=125		MIN.	5	A/ms
t_{on}	I_G=20mA I_A=200mA I_R=20mA T_j=25		TYP.	5	μs
t_{off}				30	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =22.5A t_p=380μs	T_j=25	1.5	V
V_{TO}	Threshold voltage	T_j=125	0.77	V
R_D	Dynamic resistance	T_j=125	30	mΩ
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25	5	μA
I_{RRM}		T_j=125	0.4	mA

ORDERING INFORMATION



MARKING

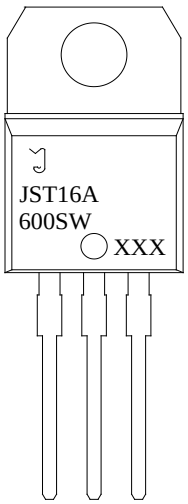
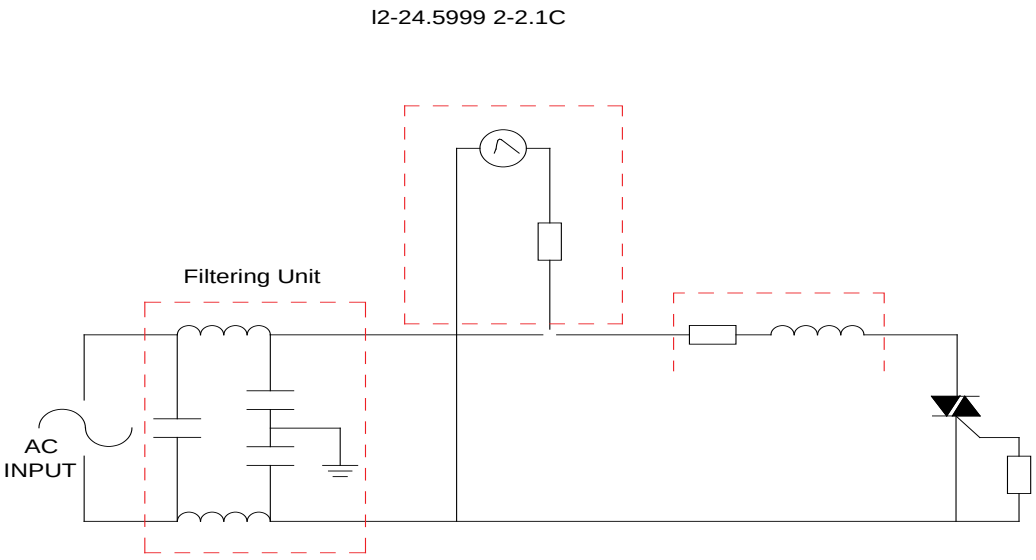
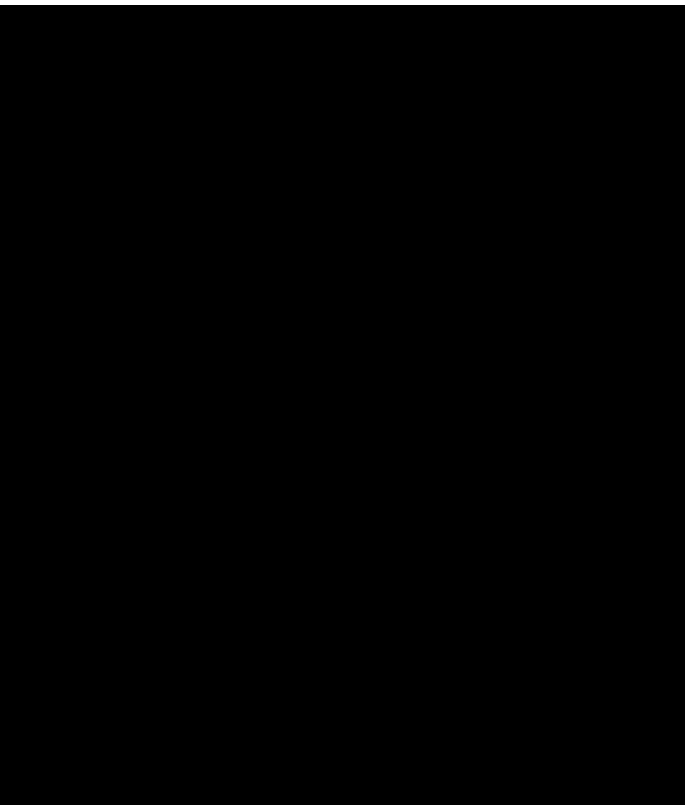


FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards





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